PF01412A

MOS FET Power Amplifier Module for E-GSM Handy Phone

HITACHI

ADE-208-477B (Z) 3rd Edition February 1997

Application

- For GSM class4 890 to 915 MHz
- For 5.5V nominal DC/DC converter use

Features

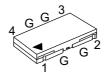
• High gain 3stage amplifier: 0 dBm input

• Lead less thin & Small package: 2 mm Max, 0.2cc

High efficiency: 45% Typ at 3.8 WWide gain control range: 90 dB Typ

Pin Arrangement

• RF-K



1: Pin 2: Vapc

2: Vapc 3: Vdd

4: Pout G: GND

Absolute Maximum Ratings $(Tc = 25^{\circ}C)$

Item	Symbol	Rating	Unit
Supply voltage	V_{DD}	10	V
Supply current	I _{DD}	3	Α
V _{APC} voltage	V_{APC}	4	V
Input power	Pin	10	mW
Operating case temperature	Tc (op)	-30 to +100	°C
Storage temperature	Tstg	-30 to +100	°C
Output power	Pout	6	W

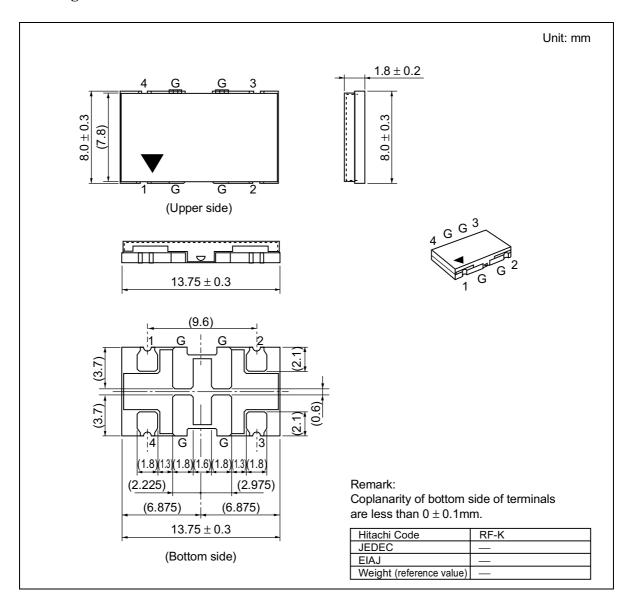


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Electrical Characteristics ($Tc = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	890	_	915	MHz	
Control voltage range	V_{APC}	0.5	_	3.0	V	
Drain cutoff current	I _{DS}	_	_	100	μΑ	V _{DD} = 10 V, V _{APC} = 0 V
Total efficiency	$\eta_{\scriptscriptstyleT}$	40	45	_	%	Pin = 1 mW, $V_{DD} = 5.5 \text{ V}$,
2nd harmonic distortion	2nd H.D.	_	–45	-35	dBc	Pout = 3.8 W, Vapc = controlled
3rd harmonic distortion	3rd H.D.		–45	-35	dBc	$R_L = Rg = 50 \Omega$, $Tc = 25^{\circ}C$
Input VSWR	VSWR (in)	_	1.5	3	_	•
Output power (1)	Pout (1)	3.8	4.5	_	W	Pin = 1 mW, V_{DD} = 5.5 V, V_{APC} = 3.0 V, R_{L} = Rg = 50 Ω, Tc = 25°C
Output power (2)	Pout (2)	2.5	3.2	_	W	Pin = 1 mW, V_{DD} = 5.0 V, V_{APC} = 3.0 V, R_{L} = Rg = 50 Ω, Tc = 80°C
Isolation	_	_	–50	-40	dBm	Pin = 1 mW, V_{DD} = 5.5 V, V_{APC} = 0.5 V, R_{L} = Rg = 50 Ω, Tc = 25°C
Switching time	tr, tf	_	1	2	μs	Pin = 1 mW, V_{DD} = 5.5 V, Pout = 3.8 W, R_{L} = Rg = 50 Ω, Tc = 25°C
Stability & Load VSWR tolerance	_	No parasitic oscillation & No degradation				Pin = 1 mW, V_{DD} = 5 to 6 V, Pout \leq 3.8 W, Vapc \leq 3 V GSM pulse. Rg = 50 Ω , t = 20 sec., Tc = 25°C, Output VSWR = 6 : 1 All phases

Package Dimensions



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